

MOSFET – P-Channel, POWER TRENCH®

-20 V, -56 A, 4 mΩ

NTTFS004P02P8

General Description

This P-Channel MOSFET is produced using onsemi's advanced POWER TRENCH process that has been optimized for $R_{DS(ON)}$, switching performance and ruggedness.

Features

- Max $R_{DS(on)}$ = 4 mΩ at $V_{GS} = -4.5$ V, $I_D = -18$ A
- Max $R_{DS(on)}$ = 5.7 mΩ at $V_{GS} = -2.5$ V, $I_D = -16$ A
- Max $R_{DS(on)}$ = 11.5 mΩ at $V_{GS} = -1.8$ V, $I_D = -11$ A
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability in a Widely Used Surface Mount Package
- This Device is Pb-Free, Halide Free and is RoHS Compliant

Applications

- Load Switch
- Battery Management
- Power Management
- Reverse Polarity Protection

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

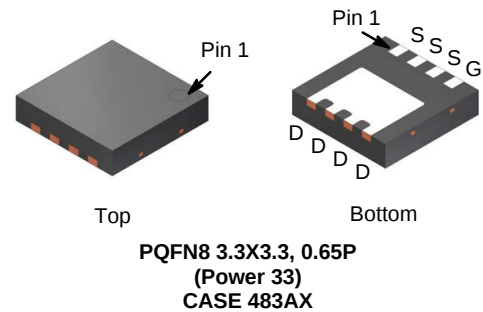
Symbol	Parameter	Ratings	Unit
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	±8	V
I_D	Drain Current – Continuous $T_C = 25^\circ\text{C}$ – Continuous $T_A = 25^\circ\text{C}$ (Note 1a) – Pulsed (Note 3)	-56 -18 -377	A
P_D	Power Dissipation $T_C = 25^\circ\text{C}$ $T_A = 25^\circ\text{C}$ (Note 1a)	40 2.3	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

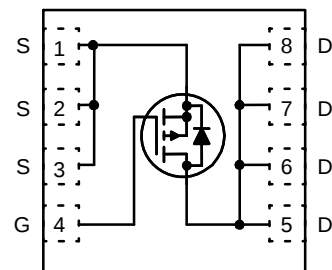
THERMAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.1	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

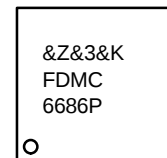
V_{DS}	$R_{DS(on)}$ MAX	I_D MAX
-20 V	4 mΩ @ -4.5 V	-56 A
	5.7 mΩ @ -2.5 V	
	11.5 mΩ @ -1.8 V	



PIN ASSIGNMENT



MARKING DIAGRAM



&Z = Assembly Plant Code
 &3 = 3-Digit Date Code (YWW)
 &K = 2-Digit Lot Traceability Code
 FDMC6686P = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
NTTFS004P02P8	PQFN8 (Power 33) (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTTFS004P02P8

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
--------	-----------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	I _D = -250 μA, V _{GS} = 0 V	-20	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = -250 μA, referenced to 25°C	-	-15	-	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -16 V, V _{GS} = 0 V	-	-	-1	μA
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±8 V, V _{DS} = 0 V	-	-	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = -250 μA	-0.4	-0.75	-1	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = -250 μA, referenced to 25°C	-	3	-	mV/°C
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = -4.5 V, I _D = -18 A	-	3.3	4	mΩ
		V _{GS} = -2.5 V, I _D = -16 A	-	4.1	5.7	
		V _{GS} = -1.8 V, I _D = -11 A	-	6	11.5	
		V _{GS} = -4.5 V, I _D = -18 A, T _J = 125°C	-	4.3	6.5	
g _{FS}	Forward Transconductance	V _{DS} = -5 V, I _D = -18 A	-	116	-	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	-	8800	13200	pF
C _{oss}	Output Capacitance		-	1520	2280	pF
C _{rss}	Reverse Transfer Capacitance		-	1340	2010	pF
R _g	Gate Resistance		-	6.2	-	Ω

SWITCHING CHARACTERISTICS

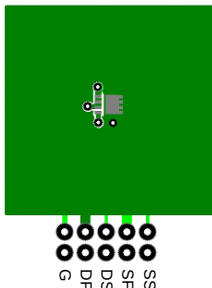
t _{d(on)}	Turn-On Delay Time	V _{DD} = -10 V, I _D = -18 A, V _{GS} = -4.5 V, R _{GEN} = 6 Ω	-	25	40	ns
t _r	Rise Time		-	77	122	ns
t _{d(off)}	Turn-Off Delay Time		-	317	506	ns
t _f	Fall Time		-	178	285	ns
Q _g	Total Gate Charge	V _{DD} = -10 V, I _D = -18 A, V _{GS} = -4.5 V	-	87	122	nC
Q _{gs}	Gate to Source Charge		-	14	-	nC
Q _{gd}	Gate to Drain "Miller" Charge		-	24	-	nC

DRAIN-SOURCE CHARACTERISTICS

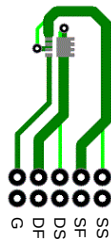
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = -18 A (Note 2)	-	-0.7	-1.2	V
		V _{GS} = 0 V, I _S = -2 A (Note 2)	-	-0.6	-1.2	
t _{rr}	Reverse Recovery Time	I _F = -18 A, di/dt = 100 A/μs	-	38	61	ns
Q _{rr}	Reverse Recovery Charge		-	24	39	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. R_{θJA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.



a. 53°C/W when mounted on a 1 in² pad of 2 oz copper



b. 125°C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Pulse I_d refers to Forward Bias Safe Operation Area.

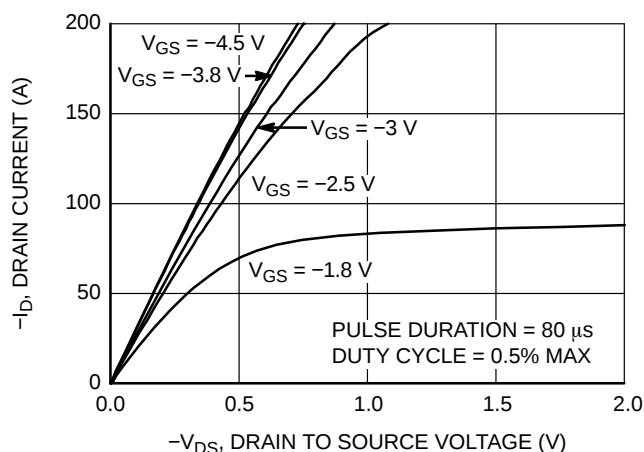
TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 1. On-Region Characteristics

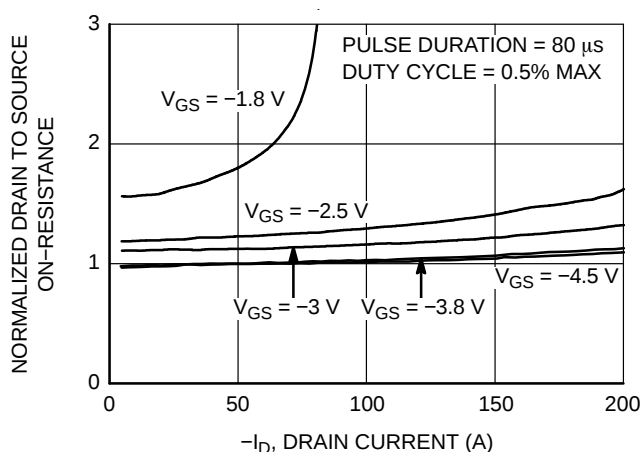


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

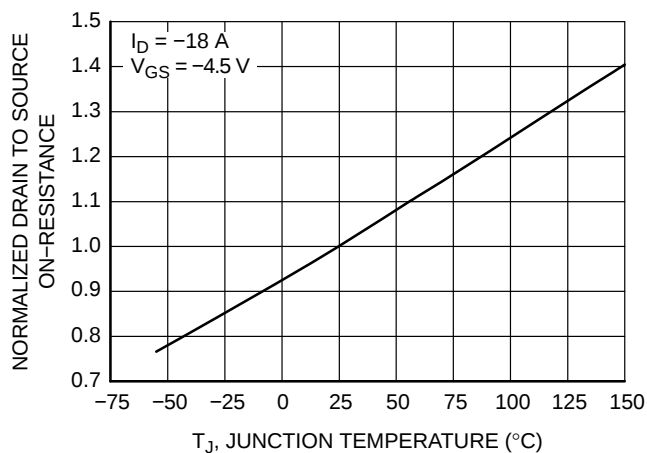


Figure 3. Normalized On-Resistance vs. Junction Temperature

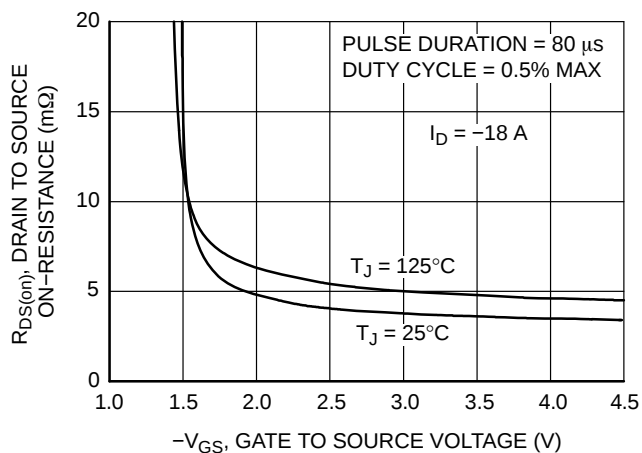


Figure 4. On-Resistance vs. Gate to Source Voltage

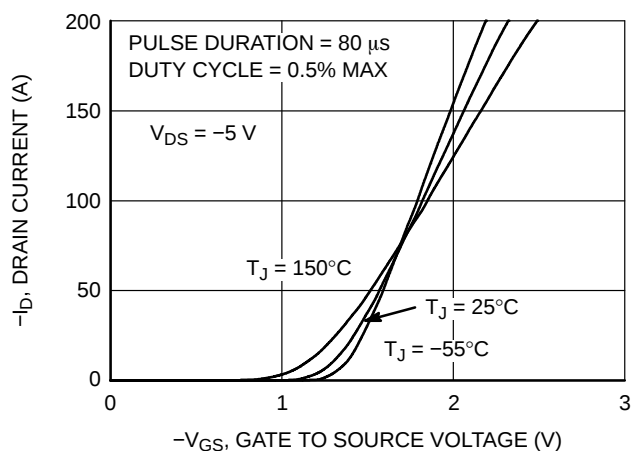


Figure 5. Transfer Characteristics

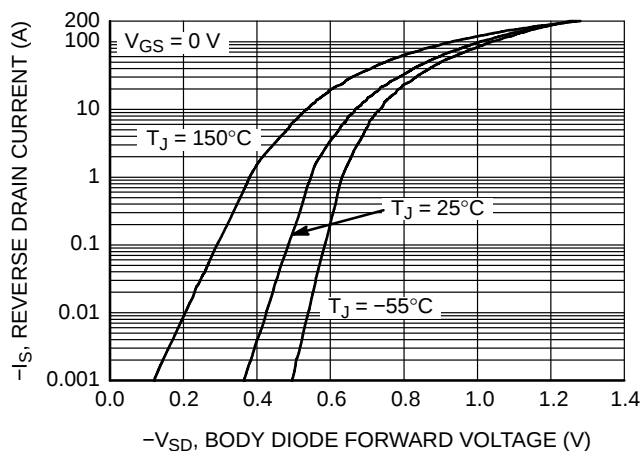


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted) (continued)

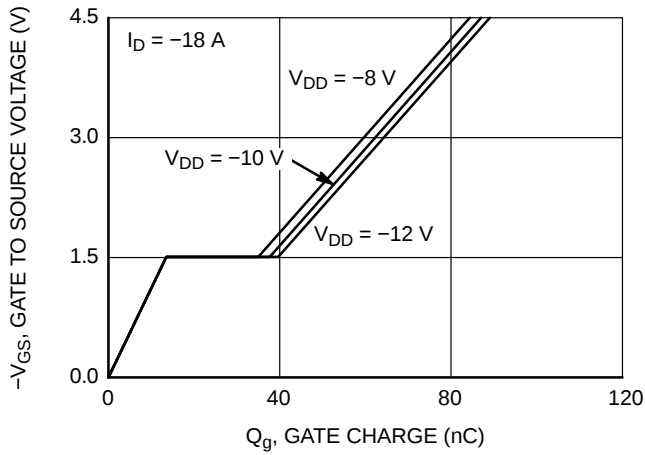


Figure 7. Gate Charge Characteristics

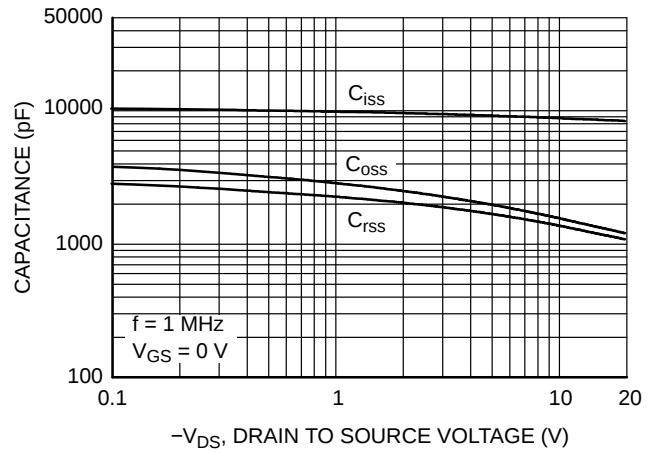


Figure 8. Capacitance vs. Drain to Source Voltage

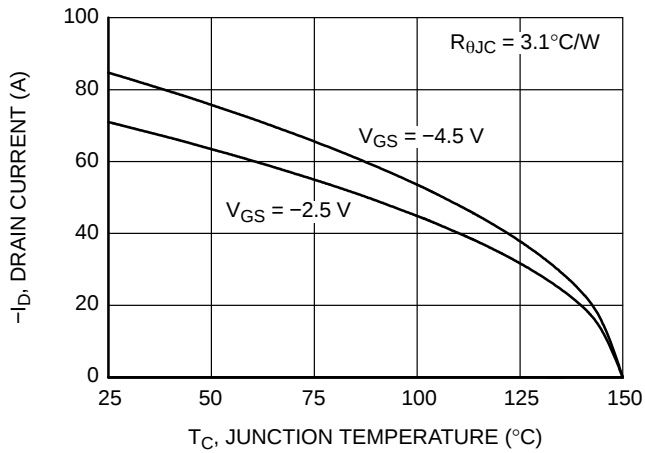


Figure 9. Maximum Continuous Drain Current vs. Case Temperature

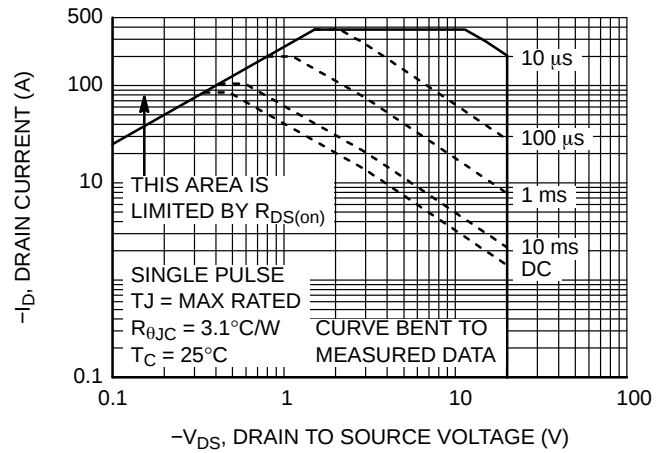


Figure 10. Forward Bias Safe Operating Area

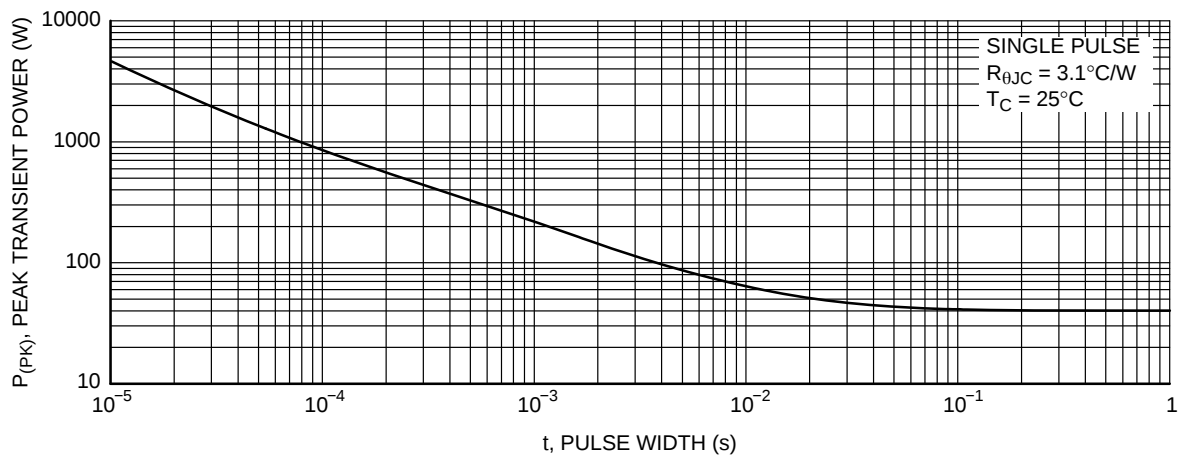
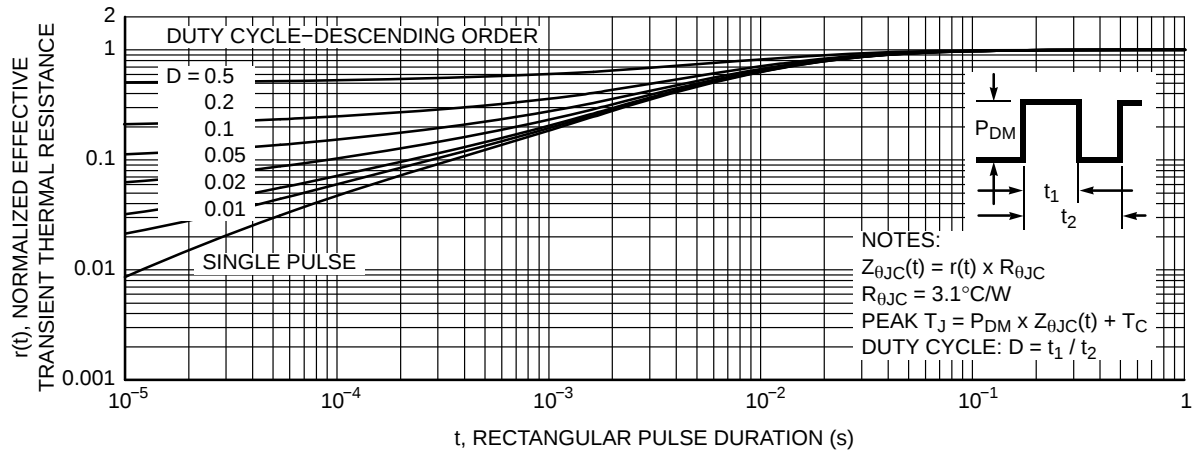
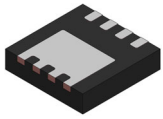


Figure 11. Single Pulse Maximum Power Dissipation

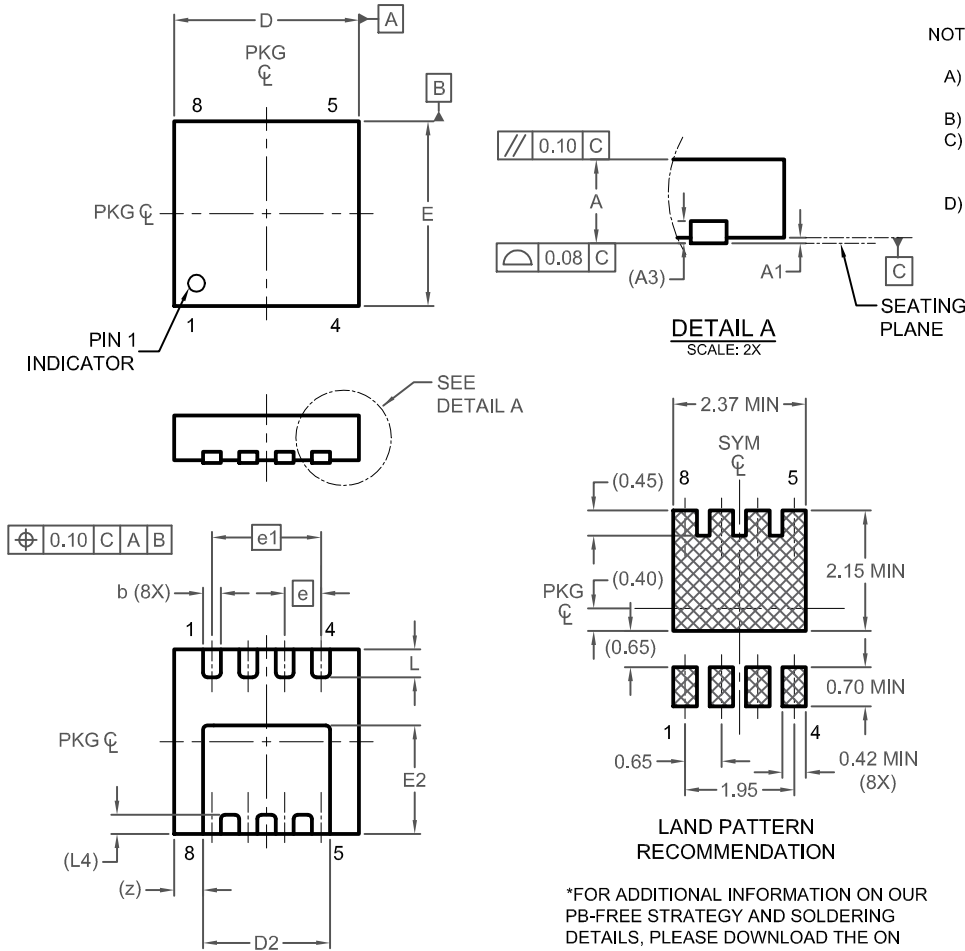
TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted) (continued)





PQFN8 3.3X3.3, 0.65P
CASE 483AX
ISSUE B

DATE 24 JUN 2022



NOTES: UNLESS OTHERWISE SPECIFIED

- A) PACKAGE STANDARD REFERENCE:
 JEDEC MO-240, ISSUE A, VAR. BA,
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONS DO NOT INCLUDE BURRS
 OR MOLD FLASH. MOLD FLASH OR
 BURRS DOES NOT EXCEED 0.10MM.
 D) DIMENSIONING AND TOLERANCING PER
 ASME Y14.5M-2009.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.20 REF		
b	0.27	0.32	0.37
D	3.20	3.30	3.40
D2	2.17	2.27	2.37
E	3.20	3.30	3.40
E2	1.84	1.94	2.04
e	0.65 BSC		
e1	1.95 BSC		
L	0.40	0.50	0.60
L4	0.34 REF		
z	0.52 REF		

*FOR ADDITIONAL INFORMATION ON OUR
 PB-FREE STRATEGY AND SOLDERING
 DETAILS, PLEASE DOWNLOAD THE ON
 SEMICONDUCTOR SOLDERING AND
 MOUNTING TECHNIQUES REFERENCE
 MANUAL, SOLDERM/D.

DOCUMENT NUMBER:	98AON13673G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	PQFN8 3.3X3.3, 0.65P	PAGE 1 OF 1

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales